



CLAIMS

1. A ceramic substrate, for a semiconductor
producing/examining device, having a conductor formed inside
5 thereof or on the surface thereof,
wherein said ceramic substrate has been sintered such that
a fractured section thereof exhibits intergranular fracture.
2. The ceramic substrate for a semiconductor
10 producing/examining device according to claim 1,
wherein an average diameter of ceramic grains of said
fractured section is 0.5 to 10 μm .
3. The ceramic substrate for a semiconductor
15 producing/examining device according to claim 1,
wherein an impurity element is locally distributed in
boundaries of ceramic grains of said fractured section.
4. The ceramic substrate for a semiconductor
20 producing/examining device according to claim 1,
wherein thermal conductivity of said ceramic substrate
is 100 W/m \cdot K or more.
5. The ceramic substrate for a semiconductor
25 producing/examining device according to claim 1,
wherein said ceramic substrate is constituted such that:
an impurity-existent area where an impurity element is
locally distributed in triple points of crystal grains, and
an impurity element-nonexistent area where an impurity
30 is not locally distributed in the triple points of the crystal
grains,
coexist therein.

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Related Pending Application

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